



**Electrical Characteristics** ( $T_J=25^\circ\text{C}$  unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
<b>Off Characteristic</b>						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	30	-	-	V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=30V, V_{GS}=0V,$	-	-	1.0	$\mu A$
$I_{GSS}$	Gate to Body Leakage Current	$V_{DS}=0V, V_{GS}=\pm 20V$	-	-	$\pm 100$	nA
<b>On Characteristics</b>						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0	2.0	3.0	V
$R_{DS(on)}$	Static Drain-Source on-Resistance note2	$V_{GS}=10V, I_D=4A$		44	59	m $\Omega$
		$V_{GS}=4.5V, I_D=3A$	-	60	65	
<b>Dynamic Characteristics</b>						
$C_{iss}$	Input Capacitance	$V_{DS}=15V, V_{GS}=0V,$ $f=1.0MHz$		183		pF
$C_{oss}$	Output Capacitance		-	44	-	pF
$C_{rSS}$	Reverse Transfer Capacitance		-	33	-	pF
$Q_g$	Total Gate Charge	$V_{DS}=15V, I_D=2A,$ $V_{GS}=10V$	-	3	-	nC
$Q_{gs}$	Gate-Source Charge		-	0.5	-	nC
$Q_{gd}$	Gate-Drain("Miller") Charge		-	0.8	-	nC
<b>Switching Characteristics</b>						
$t_{d(on)}$	Turn-on Delay Time	$V_{DS}=15V,$ $I_D=4A, R_{GEN}=3\Omega,$ $V_{GS}=10V$	-	4	-	ns
$t_r$	Turn-on Rise Time		-	2.1	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	15	-	ns
$t_f$	Turn-off Fall Time		-	3.2	-	ns
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
$I_S$	Maximum Continuous Drain to Source Diode Forward Current					A
$I_{SM}$	Maximum Pulsed Drain to Source Diode Forward Current		-	-	16	A
$V_{SD}$	Drain to Source Diode Forward Voltage	$V_{GS}=0V, I_S=4A$	-	-	1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. Pulse Test: Pulse Width $\leq 300\mu s$ , Duty Cycle $\leq 0.5\%$

## Typical Performance Characteristics

Figure 1: Output Characteristics

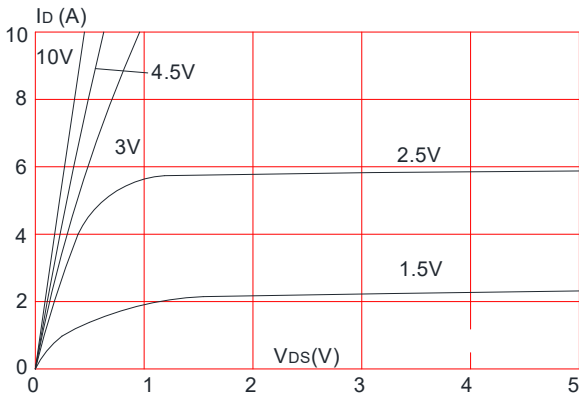


Figure 2: Typical Transfer Characteristics

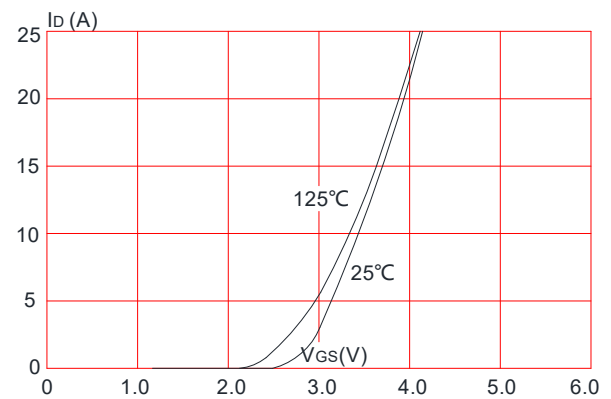


Figure 3: On-resistance vs. Drain Current

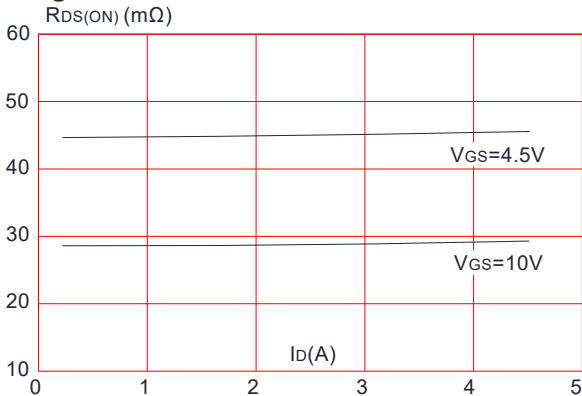


Figure 4: Body Diode Characteristics

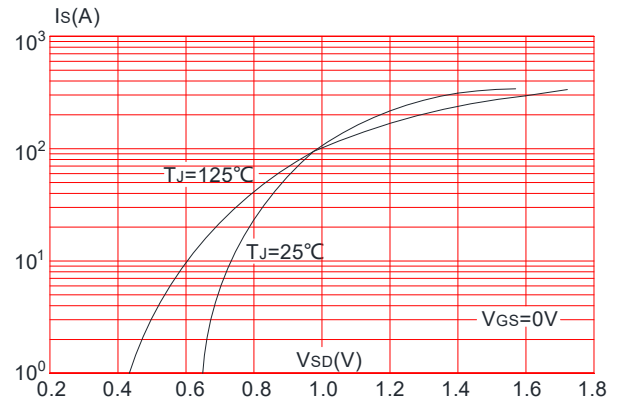


Figure 5: Gate Charge Characteristics

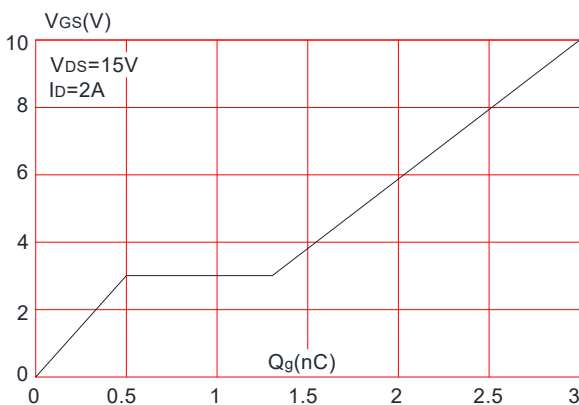
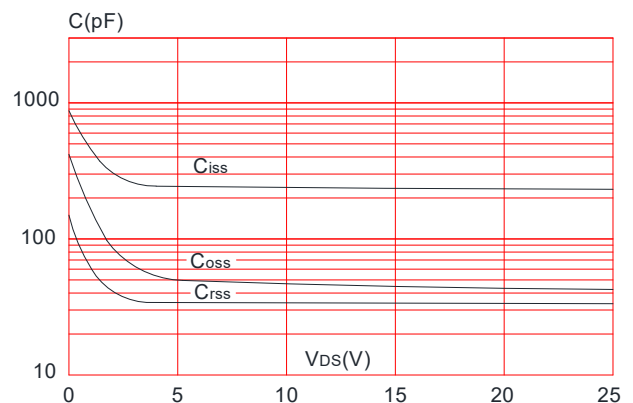


Figure 6: Capacitance Characteristics



TM04N03I

N-Channel Enhancement Mosfet

Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

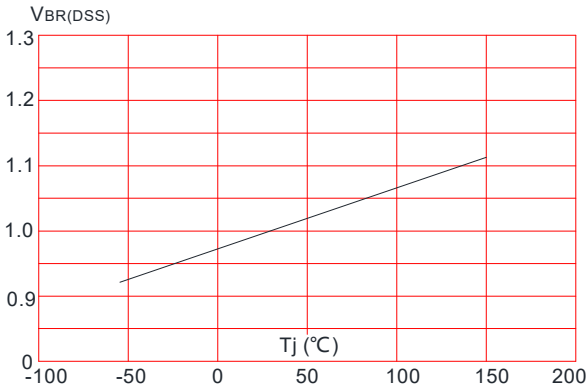


Figure 8: Normalized on Resistance vs. Junction Temperature

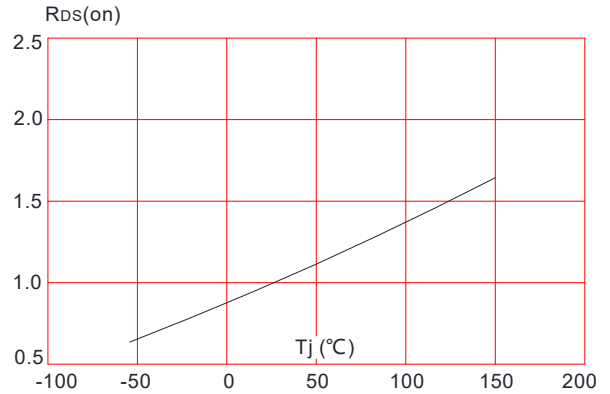


Figure 9: Maximum Safe Operating Area

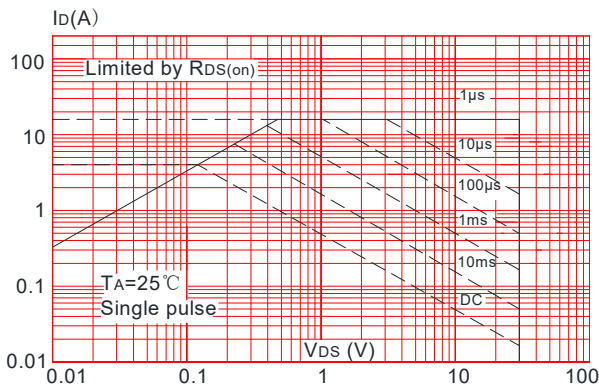


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

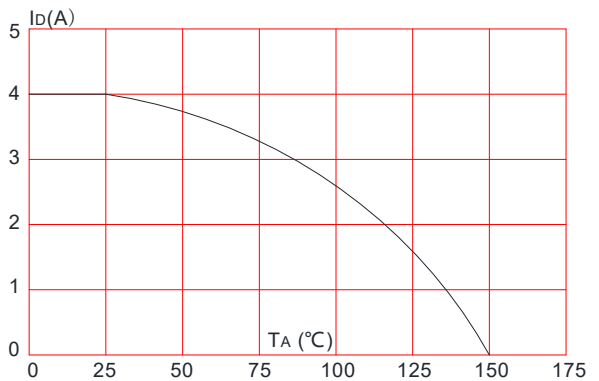
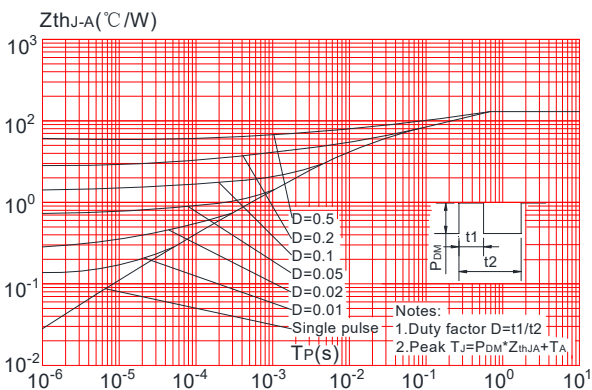
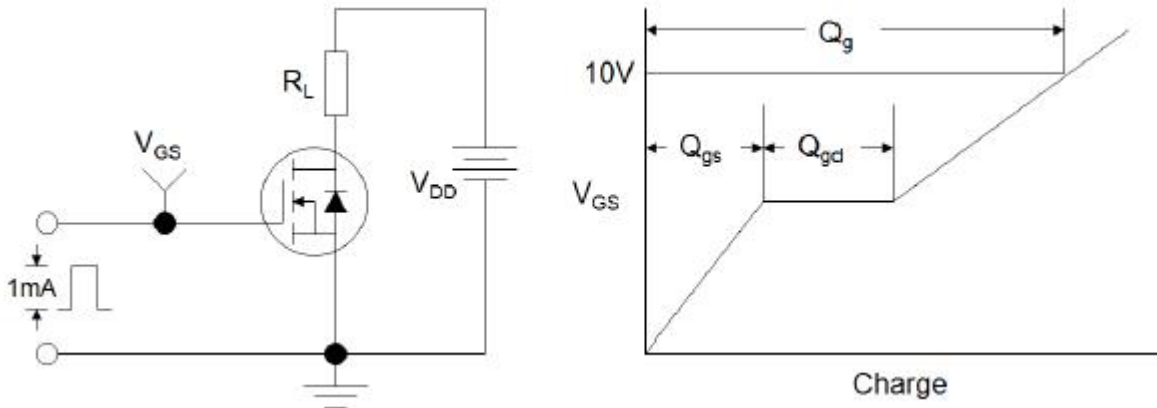


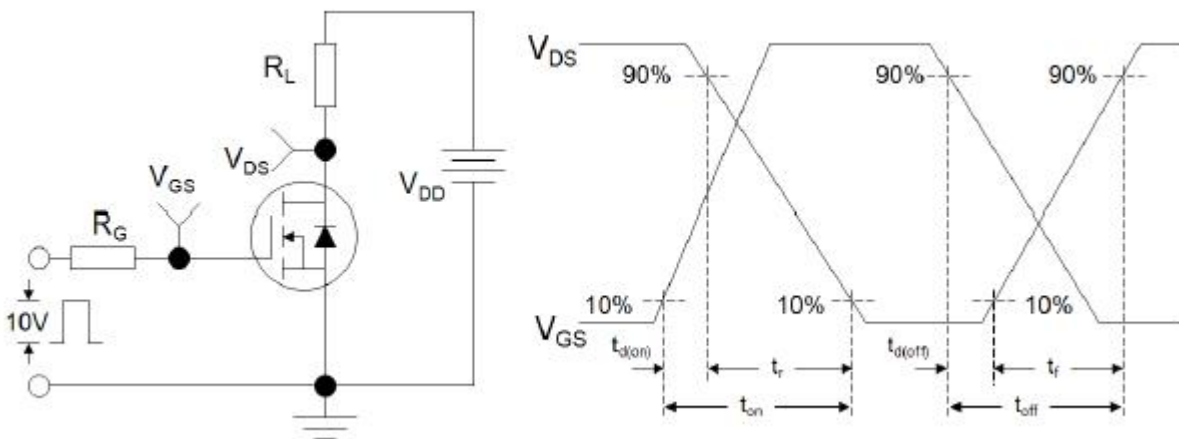
Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



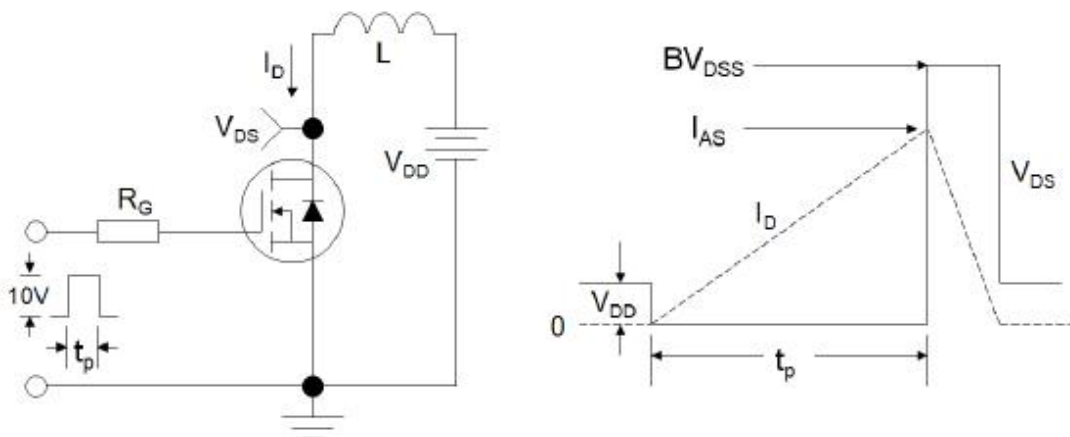
**Test Circuit**



**Figure1:Gate Charge Test Circuit & Waveform**

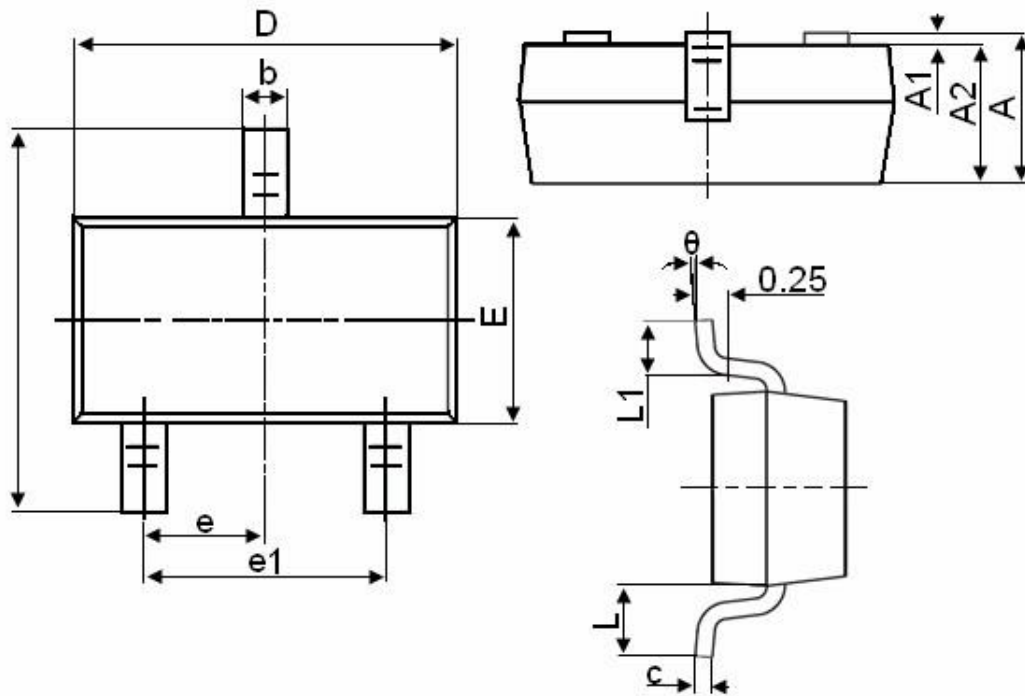


**Figure 2: Resistive Switching Test Circuit & Waveforms**



**Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms**

### Package Information: SOT-23



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
qm	oÃp=	oËp=